

Jimy J Encomendero-Risco

List of Publications by Citations

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16

papers

153

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ext. papers

202

ext. citations

3.6

avg, IF

2.61

L-index

#	Paper	IF	Citations
16	Room temperature microwave oscillations in GaN/AlN resonant tunneling diodes with peak current densities up to 220 kA/cm ² . <i>Applied Physics Letters</i> , 2018 , 112, 103101	3.4	38
15	New Tunneling Features in Polar III-Nitride Resonant Tunneling Diodes. <i>Physical Review X</i> , 2017 , 7,	9.1	34
14	Broken Symmetry Effects due to Polarization on Resonant Tunneling Transport in Double-Barrier Nitride Heterostructures. <i>Physical Review Applied</i> , 2019 , 11,	4.3	17
13	Metal-ion effects on the polarization of metal-bound water and infrared vibrational modes of the coordinated metal center of Mycobacterium tuberculosis pyrazinamidase via quantum mechanical calculations. <i>Journal of Physical Chemistry B</i> , 2014 , 118, 10065-75	3.4	17
12	Terahertz amplification in RTD-gated HEMTs with a grating-gate wave coupling topology. <i>Applied Physics Letters</i> , 2016 , 109, 063111	3.4	12
11	Fighting Broken Symmetry with Doping: Toward Polar Resonant Tunneling Diodes with Symmetric Characteristics. <i>Physical Review Applied</i> , 2020 , 13,	4.3	8
10	Direct electrical observation of plasma wave-related effects in GaN-based two-dimensional electron gases. <i>Applied Physics Letters</i> , 2014 , 105, 173508	3.4	6
9	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 119, 162104	3.4	6
8	N-polar GaN/AlN resonant tunneling diodes. <i>Applied Physics Letters</i> , 2020 , 117, 143501	3.4	5
7	Comparison of unit cell coupling for grating-gate and high electron mobility transistor array THz resonant absorbers. <i>Journal of Applied Physics</i> , 2018 , 124, 093101	2.5	4
6	Gallium nitride tunneling field-effect transistors exploiting polarization fields. <i>Applied Physics Letters</i> , 2020 , 116, 073502	3.4	2
5	2017 ,		1
4	New physics in GaN resonant tunneling diodes 2019 ,		1
3	Resonant Tunneling Transport in Polar III-Nitride Heterostructures 2020 , 215-247		1
2	Molecular beam epitaxy of polar III-nitride resonant tunneling diodes. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021 , 39, 023409	2.9	1
1	Epitaxial Ferrimagnetic Mn ₄ N Thin Films on GaN by Molecular Beam Epitaxy. <i>IEEE Transactions on Magnetics</i> , 2021 , 1-1	2	0